



DCR4910W28

Phase Control Thyristor

Replaces DS5775-2 DS5775-3 January 2022 (LN41443)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
DCR4910W28 DCR4910W26 DCR4910W24	2800 2600 2400	Tvj = -40°C to 125°C, IDRM = IRRM = 200mA, VDRM, VRRM tp = 10ms VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR4910W28

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V DRM	2800V
IT(AV)	4670A
Ітѕм	63000A
dV/dt*	2000V/μs
dl/dt	500A/μs

^{*} Higher dV/dt selections are available on request

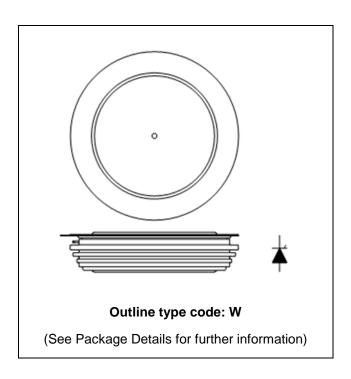


Fig. 1 Package outline

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CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
İT(AV)	Mean on-state current	Half wave resistive load	4670	А
It(RMS)	RMS value	-	7340	А
lτ	Continuous (direct) on-state current	-	6670	Α

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	63.0	kA
l²t	I2t for fusing	V _R = 0	19.8	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	6.3	°C/kW
Rth(j-c)	Rth(j-c) Thermal resistance - junction to case	Cingle side and a	Anode DC	-	11.2	°C/kW
		Single side cooled	Cathode DC	-	14.5	°C/kW
D	The second are interest and the state in large	Clamping force 76kN	Double side	-	1.4	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	2.8	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			68	84	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	200	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.15	1.30	٧
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, g	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	250	A/µs
ui/at	ivate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	500	A/µs
V	Threshold voltage - Low level	500A to 3000A at Tcase = 125°C		-	0.79	٧
V т(то)	Threshold voltage - High level	3000A to 7000A at Tcase = 125°C		-	0.91	٧
_	On-state slope resistance - low level	500A to 3000A at Tcase = 125°C		-	0.14	mΩ
ľτ	On-state slope resistance - High level	3000A to 7000A at Tcase = 125°C		-	0.10	mΩ
tgd	Delay time	V_D = 67% V_{DRM} , gate source 30V, 10Ω t_T = 0.5 μ s, T_j = 25°C		0.5	1.5	μs
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/ μ s, $dV_{DR}/dt = 20$ V/ μ s linear		100	250	μs
Qs	Stored charge	T _j = 125°C, dl/dt = 1A/μs		540	2030	μC
IRR	Reverse recovery current	VR(peak) ~ 1700V, VRM ~ 1100V		18	35	А
lι	Latching current	Tj = 25°C, V _D = 5V		-	3	А
Ін	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 50	0A, Ιτ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	٧
V GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Ідт	Gate trigger current	VDRM = 5V, Tcase = 25°C	250	mA
lgp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

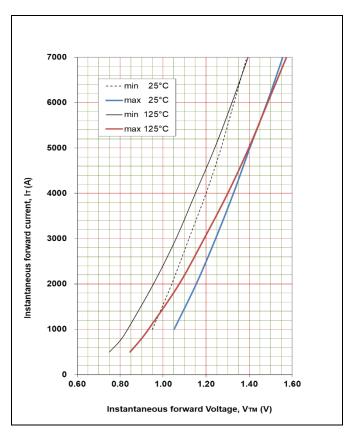


Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.885853

B = -0.051875

C = 0.000018

D = 0.012229

These values are valid for T_j = 125°C for I_T 500A to 7000A

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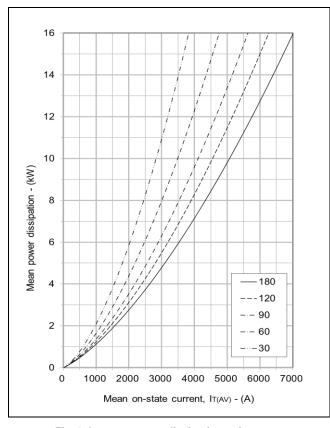


Fig. 3 On-state power dissipation - sine wave

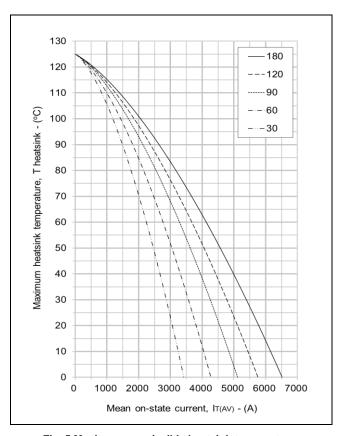


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

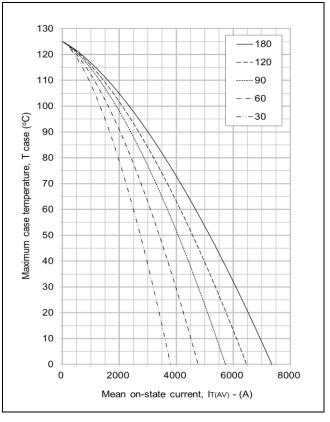


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

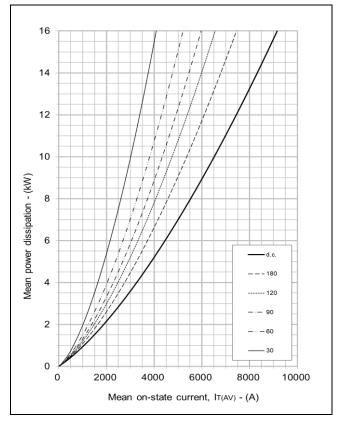


Fig. 6 On-state power dissipation - rectangular wave

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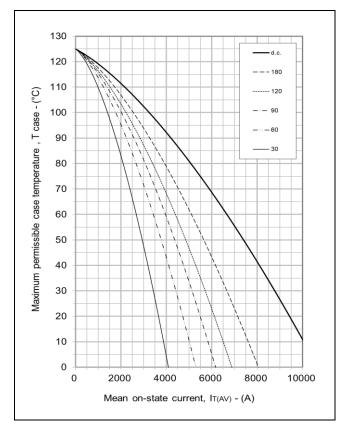
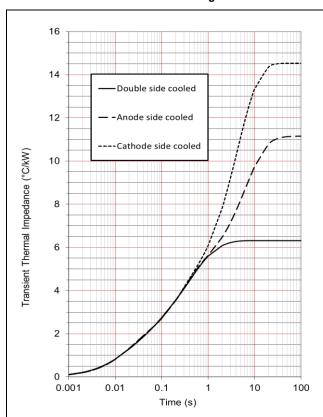


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



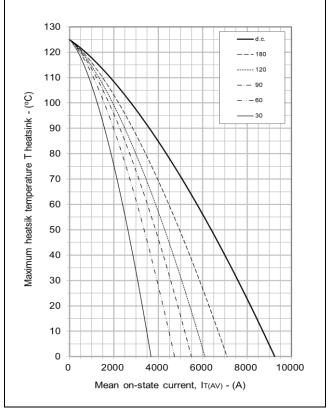


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.882	1.299	2.805	1.331
cooled	Ti(s)	0.011	0.058	0.358	1.129
Anode side	Ri(°C/kW)	1.520	3.240	5.762	0.631
cooled	Ti(s)	0.017	0.242	6.013	15.364
Cathode side	Ri(°C/kW)	1.411	2.467	6.745	3.905
cooled	Ti(s)	0.016	0.179	3.620	6.196

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}(j-c)}$ when the device operates at conduction angles other than d.c.

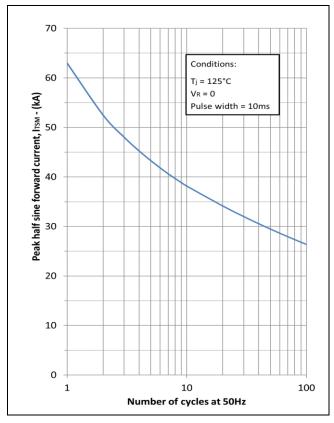
Double side cooling					Anode Side	Coolin
	ΔZ_{th}	(z)			ΔZ_{i}	h (Z)
θ°	sine.	rect.		θ°	sine.	re
180	1.00	0.67		180	0.94	0.
120	1.16	0.97		120	1.08	0.
90	1.33	1.13		90	1.23	1.
60	1.48	1.31		60	1.37	1.
30	1.61	1.51		30	1.47	1.
15	1.66	1.61	1	15	1.52	- 1

Ca	thode Sided Cooling			
	$\Delta Z_{th}(z)$			
θ°	sine.	rect.		
180	0.95	0.65		
120	1.09	0.92		
90	1.25	1.07		
60	1.38	1.23		
30	1.49 1.40			
15	1.54	1.49		

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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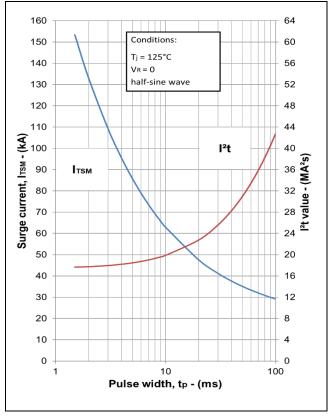


Fig. 10 Multi-cycle surge current

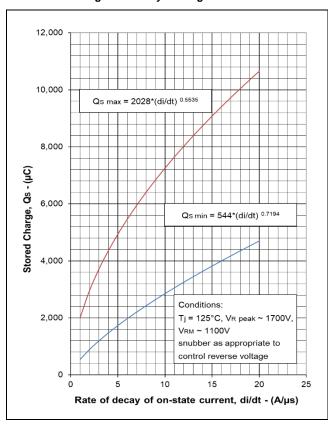


Fig. 12 Reverse recovery charge

Fig. 11 Single-cycle surge current

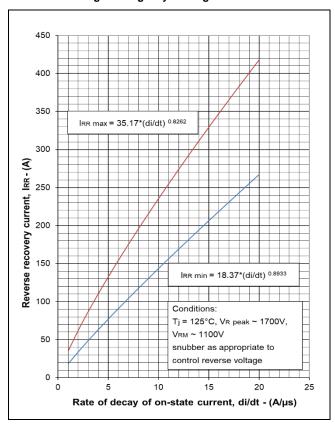


Fig. 13 Reverse recovery current

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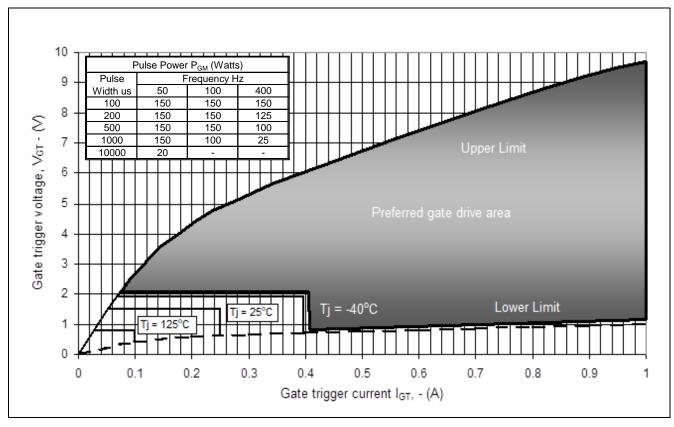


Fig. 14 Gate characteristics

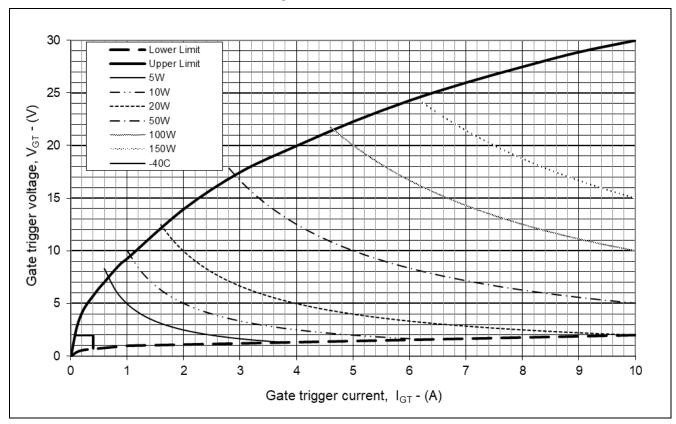


Fig. 15 Gate characteristics

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

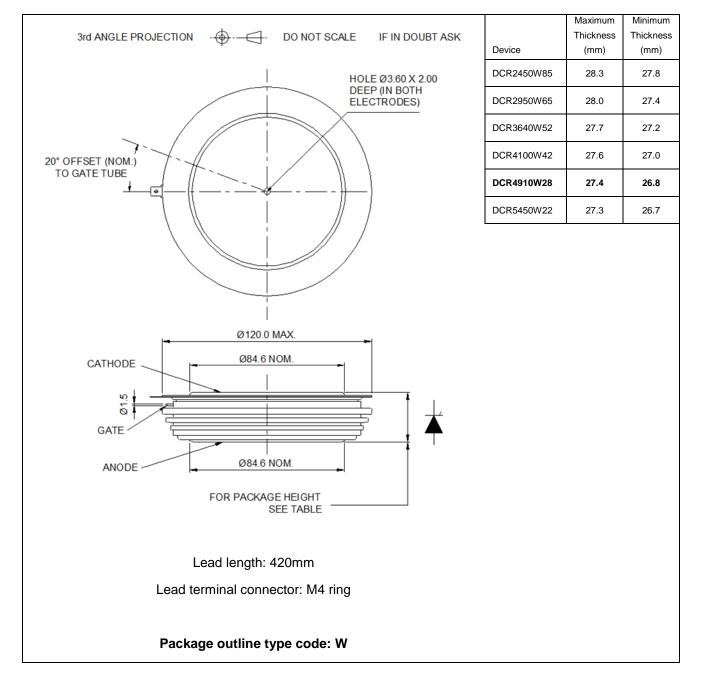


Fig. 16 Package outline

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